

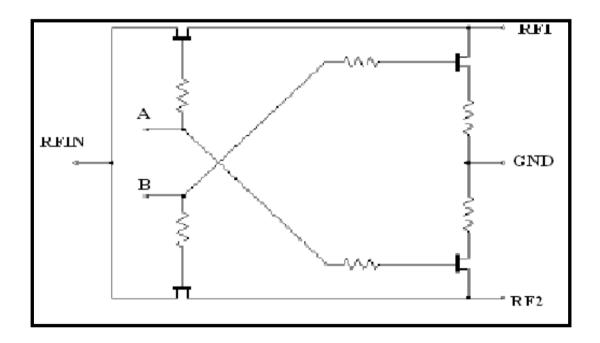
### **Product Description**

The RBS681 is a high performance Gallium Arsenide single pole double through broad band RF switch suitable for use in broadband communications and instrumentation applications. The isolated port of the switch is terminated with a 50 ohm load. The switch is controlled by the application of complimentary 0V/-5V or 0/-8V signals to the control lines in accordance with the truth table below.

#### **Features**

- Broadband performance
- Low Insertion Loss; 0.6 dB typ at 1 GHz
- Ultra low DC power consumption
- 50 Ω output terminations

### **Functional Block Diagram**





### **Specifications**

### **Absolute Maximum Ratings**

Name	Description	
Max Control Voltage	-8 V	
RF I/P Power	+33 dBm	
Operating Temperature Range	-40 to +85° C	

### **Electrical Performance**

### Typical performance at 25°C

Ambient temperature =  $25\pm3^{\circ}$ C, Zo =  $50\ \Omega$ , Control voltage = 0V/-5V unless otherwise stated

Parameter	Condition	Min.	Тур.	Max.	Units
Insertion Loss <sup>1</sup>	DC – 0.5 GHz	1	0.45	0.6	dB
	0.5 – 2 GHz	-	0.6	1.0	dB
Isolation <sup>1</sup>	DC – 0.5 GHz	33	35	-	dB
	0.5 – 2 GHz	23	24	-	dB
Input Return Loss <sup>2</sup>	DC – 0.5 GHz	30	32	-	dB
	0.5 – 2 GHz	21	22	-	dB
Output Return Loss <sup>2</sup>	DC – 0.5 GHz	30	32	-	dB
	0.5 – 2 GHz	21	22	-	dB
P1dB power compression point <sup>3</sup>	0/-5 V control; 50 MHz	19	21.5	-	dBm
	0/-5 V control; 2 GHz	21	23	-	dBm
	0/-8 V control; 50 MHz	21	23	-	dBm
	0/-8 V control; 2 GHz	29	31	-	dBm
Switching Speed	50% control to 10%90% RF	-	2.2	-	ns

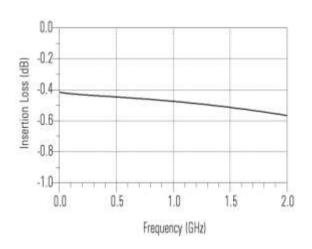
### Notes

- 1. Insertion loss and Isolation measured between RF Input and any output.
- 2. Return Loss measured in low loss switch state.
- 3. Input power at which insertion loss compresses by 1dB.

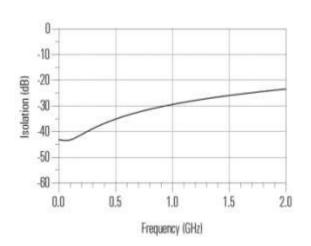


# **Preliminary Data**

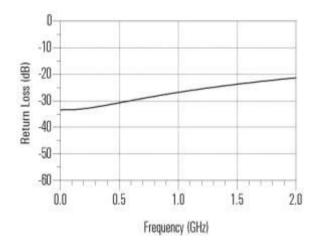
### **Insertion Loss**



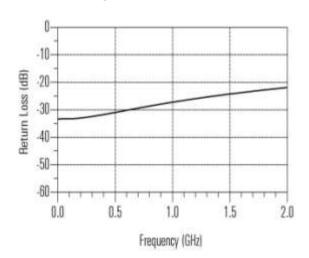
### **Isolation**



# **Input Return Loss**

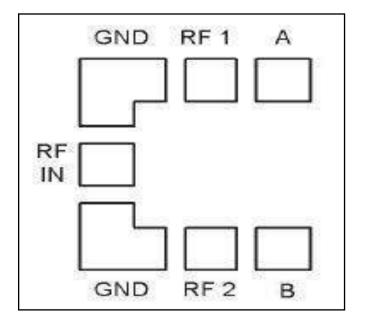


### **Output Return Loss**





# **Chip Outline Diagram**



Die size: 1.0 X 1.5 mm

Minimum Bond pad size: 120 μm x 120 μm

Die thickness: 200 μm

# **Switching Truth Table**

A	В	<b>RFIN-RF1</b>	<b>RFIN-RF2</b>
0 V	-5 V	Low Loss	Isolated
-5 V	0 V	Isolated	Low Loss



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#### **Product Preview**

The document contains information from the product concept specification. RF Arrays Inc. reserves the right to change information at any time without notification.

#### **Preliminary Information**

The document contains information from the design target specification. RF Arrays Inc. reserves the right to change information at any time without notification.

#### Production testing may not include testing of all parameters.

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